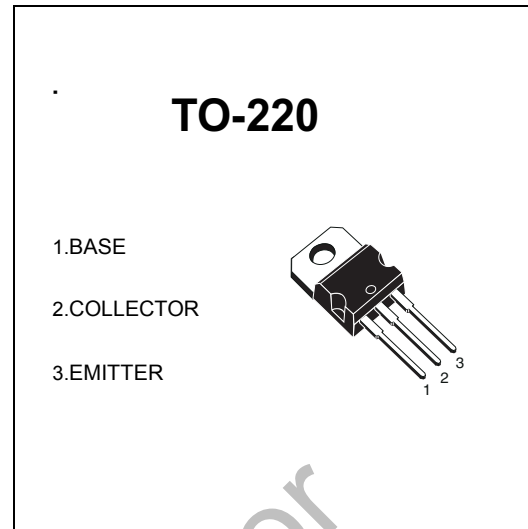


## TO-220 Plastic-Encapsulate Transistors

### TIP122 TRANSISTOR (NPN)

Part Number: 95HI F9G

- High DC Current Gain
- Electrically Similar to Popular TIP122
- Built-in a Damper Diode at E-C



Electrical Characteristics (Ta=25°C unless otherwise noted)

Symbol	Parameter	Typical Value	Unit
V <sub>76C</sub>	Collector-Base Voltage	100	V
V <sub>79C</sub>	Collector-Emitter Voltage	100	V
V <sub>96C</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current -Continuous	5	A
D <sub>7</sub>	Collector Dissipation	2	W
T <sub>stg</sub>	Junction and Storage Temperature	-55-150	°C

Electrical Characteristics (Ta=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Typical Value	Unit
V <sub>(BR)CBO</sub>	Collector-Base Voltage	I <sub>C</sub> =1mA, I <sub>E</sub> =0	100	V
V <sub>(BR)CEO</sub>	Collector-Emitter Voltage	I <sub>C</sub> =30mA, I <sub>B</sub> =0	100	V
V <sub>(BR)EBO</sub>	Emitter-Base Voltage	I <sub>E</sub> =3mA, I <sub>C</sub> =0	5	V
I <sub>CB0</sub>	Collector Current	V <sub>CB</sub> =100V, I <sub>E</sub> =0	10	μA
I <sub>CEO</sub>	Collector Current	V <sub>CE</sub> =50V, I <sub>E</sub> =0	10	μA
I <sub>EBO</sub>	Emitter Current	V <sub>EB</sub> =5V, I <sub>C</sub> =0	2	mA
h <sub>FE(2)</sub>	Current Gain	V <sub>CE</sub> =4V, I <sub>C</sub> =4A	1000	
		V <sub>CE</sub> =4V, I <sub>C</sub> =8A	100	
V <sub>CE(sat)(1)</sub>	Collector-Emitter Sat. Voltage	I <sub>C</sub> =4A, I <sub>B</sub> =16mA	2	V
		I <sub>C</sub> =8A, I <sub>B</sub> =80mA	4	V
V <sub>BE(sat)</sub>	Base-Emitter Sat. Voltage	I <sub>C</sub> =8A, I <sub>B</sub> =80mA	4.5	V
V <sub>BE</sub>	Base-Emitter Voltage	V <sub>CE</sub> =4V, I <sub>C</sub> =4A	2.8	V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=0.1MHz	200	pF

## Typical Characteristics

